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START Jic substrate Providing depositing layer supplying atmospere including exygen Performing HD plasma Process 5106 performing HD 106e HDFECUD Process primalotis Oxidation process 106h causing reactions 106 b creating reactive between gases oxygen species breaking Si-C bonds 108 Privomst 107 SiOz overlying SiC Jormina SiDa etching depositing metal

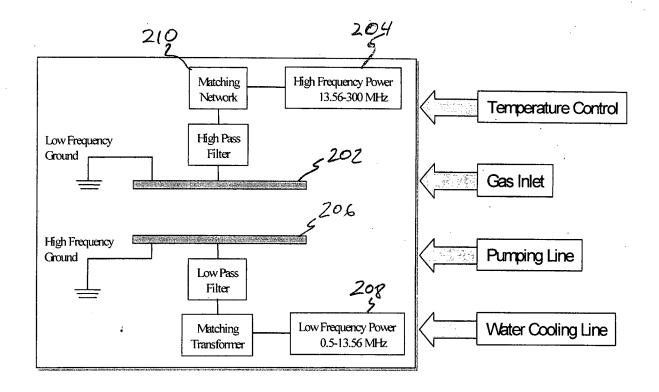


Fig. 2

Sic substrate atmosphere including oxyge Plana oxidation reactive oxygen species Si-C bonks 312 free Si atoms to reactive oxygen Species

Sic substrate Si Hy N20, and HD FEGUD POLPSS+ Causing reaction between Sases lepositing SiO2/5410

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STATES SOO

Providing SiC substrate 1502

Idepositing Si layor 1504

Supplying atmosphere including oxygen

Performing HD oxidation process

Creating reactive oxygen species 500

bonding Si atoms to reactive oxygen species

5'ubst mosphere including HD oxidation Process reactive oxygen species between SiH4, N20, and

STARTO Providing Sic substrate atmosphere including oxygen terming HD oxdation process Creating reactive oxygen species 15 free Si atoms to reative etching SiOz 15712 metal 7 314 depositing F19.7

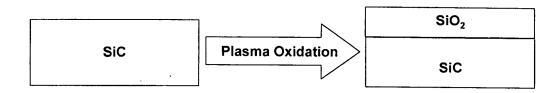


Fig. 8

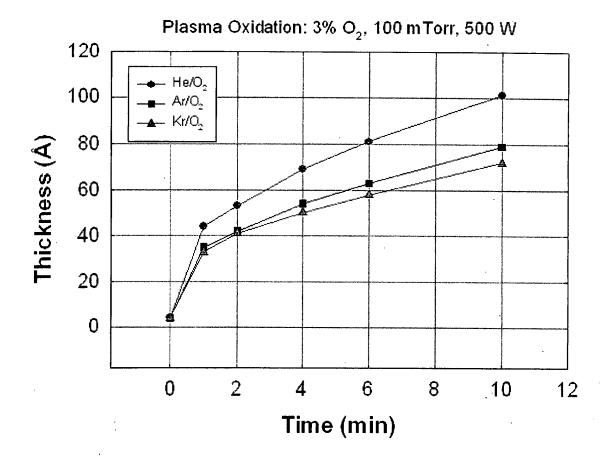


Fig. 9

HD-PECVD Deposited SiO₂

SiC

Fig. 10

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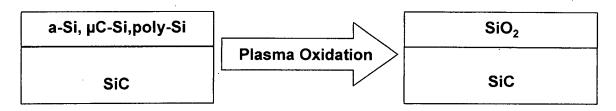


Fig. 11